

Appl. No. 10/063,779
Amdt. dated February 17, 2005
Reply to Office action of November 29, 2004

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Amendments to the Specification:

1. Please replace the title of the invention with the following amended title:

METHOD OF CORRECTING A MASK LAYOUT CRITICAL
5 DIMENSIONS OF ELEMENT PATTERNS ON A WAFER

2. Please replace paragraph [0002] with the following amended paragraph:

[0002] The present invention relates to a method of correcting ~~critical dimensions of element patterns on a wafer~~ a mask layout, and more particularly, to a method of correcting systematic errors produced during a
10 pattern transfer process on ~~element patterns on a wafer~~ a mask layout.

3. Please replace paragraph [0010] with the following amended paragraph:

[0010] It is an objective of the claimed invention to provide a method of correcting ~~critical dimensions of element patterns on a wafer~~ a mask layout to effectively prevent micro-loading effect from inducing pattern
15 transferring deviations.

4. Please replace paragraph [0011] with the following amended paragraph:

[0011] According to the claimed invention, a mask layout including a plurality of element patterns is provided. An an inspection program is executed to classify the element patterns of the [[a]] mask layout into a
20 plurality of element pattern types according to pattern deviation data of transferred element patterns onto a wafer a pattern density of the element patterns. Following this, each of the element pattern types is corrected and ~~transferred to the wafer~~ so as to prevent a plasma micro-loading effect.

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5. Please replace abstract of the present application with the following amended paragraph:

A method of correcting ~~critical dimensions of element patterns on a wafer~~ a mask layout is provided. The mask layout includes a plurality of element patterns. An inspection program is executed to classify the element patterns of the ~~[[a]]~~ mask layout into a plurality of element pattern types according to ~~pattern deviation data of transferred element patterns onto the wafer~~ a pattern density of the element patterns. Following this, each of the element pattern types is corrected ~~and transferred to the wafer~~ so as to
10 prevent a plasma micro-loading effect.